

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of

Confirmation No. 8213

HIROHAMA et al

Allowed: September 29, 2004

Serial No. 09/988,221

Atty. Ref.: 900-408

Filed: November 19, 2001

Group: 1765

Examiner: Deo, D.

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

\* \* \* \* \*

December 14, 2004

**Mail Stop: Issue Fee**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE**

The instant application was allowed September 29, 2004. However, the Reasons for Allowance are not commensurate with the scope of the claims.


For example, and without limitation, claim 9 does not require that both the second and fourth etching gas(es) consist essentially of oxygen. Instead, claim 9 requires that one or more (i.e., at least one of) of the second and fourth gas(es) consists essentially of oxygen

Please let me know if you should have any questions.

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Respectfully submitted,

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